

ABSTRACT

A method for manufacturing a semiconductor device according to an aspect of the present disclosure includes a step of preparing a dicing/die-bonding integrated film including an adhesive layer formed of a heat-curable resin composition having a melt viscosity of 3100 Pa·s or higher at 120°C, a tacky adhesive layer, and a base material film; a step of sticking a surface on the adhesive layer side of the dicing/die-bonding integrated film and a semiconductor wafer together; a step of dicing the semiconductor wafer; a step of expanding the base material film and thereby obtaining adhesive-attached semiconductor elements; a step of picking up the adhesive-attached semiconductor element from the tacky adhesive layer; a step of laminating this semiconductor element to another semiconductor element, with the adhesive interposed therebetween; and a step of heat-curing the adhesive.

Fig. 1